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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Didier DUTARTRE and Patrick JERIER  
Serial No: 09/902,497  
Filed: July 10, 2001  
For: METHOD OF EPITAXY ON A SILICON SUBSTRATE COMPRISING  
AREAS HEAVILY DOPED WITH ARSENIC

Examiner: Unassigned  
Art Unit: 1762

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

The undersigned hereby certifies that this document is being placed in the United States mail with first-class postage attached, addressed to Box Missing Parts, Commissioner for Patents, Washington, D.C. 20231 on December 18, 2001.

  
Eileen Casey

Box Missing Parts  
Commissioner For Patents  
Washington, D.C. 20231

Sir:

**PRELIMINARY AMENDMENT**

Prior to examination, please amend this application as follows:

**IN THE CLAIMS**

✓  
Please cancel claims 1-9 without prejudice or disclaimer.

Please add the following new claims.

10. A method of vapor phase epitaxial deposition of silicon on a silicon substrate including areas containing dopants at high concentration, while avoiding an autodoping of the epitaxial layer by the dopants, including the steps of:

- a) performing a first epitaxial deposition;  
b) performing an anneal after step a);